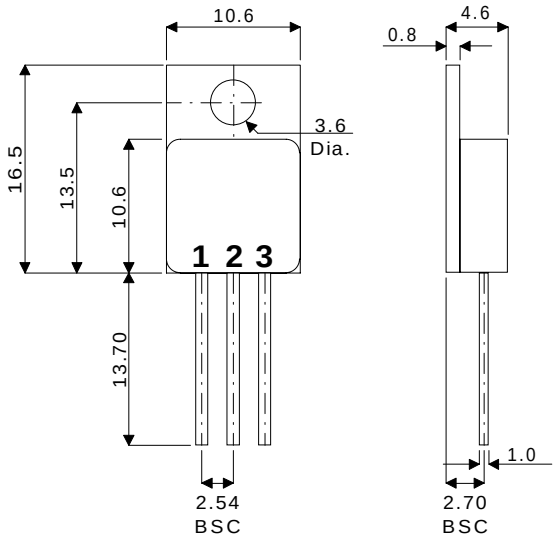
SB16-100M
SB16-100AM
SB16-100RM

DUAL SCHOTTKY BARRIER DIODE IN TO220 METAL PACKAGE FOR HI–REL APPLICATIONS

MECHANICAL DATA
Dimensions in mm

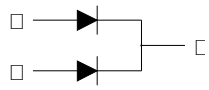
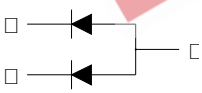
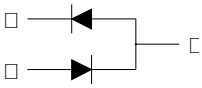


TO220 METAL PACKAGE

FEATURES

- HERMETIC TO220 METAL PACKAGE
- ISOLATED CASE
- SCREENING OPTIONS AVAILABLE
- OUTPUT CURRENT 16A
- LOW V_F
- LOW LEAKAGE

ELECTRICAL CONNECTIONS

Common Cathode	Common Anode	Series Connection
SB16-100M	SB16-100AM	SB16-100RM
		
1 = A_1 Anode 1 2 = K Cathode 3 = A_2 Anode 2	1 = K_1 Cathode 1 2 = A Anode 3 = K_2 Cathode 2	1 = K_1 Cathode 1 2 = Centre Tap 3 = A_2 Anode

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)		SB16-100M SB16-100AM SB16-100RM
V_{RRM}	Peak Repetitive Reverse Voltage	100V
V_{RSM}	Peak Non-Repetitive Reverse Voltage	100V
V_R	Continuous Reverse Voltage	100V
I_O	Output Current	16A
I_{FSM}	Peak Non-Repetitive Surge Current (50Hz)	245A
T_{STG}	Storage Temperature Range	-55°C to 150°C
T_J	Maximum Operating Junction Temperature	150°C/W

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SEME LAB

SB16-100M
SB16-100AM
SB16-100RM

ELECTRICAL CHARACTERISTICS (Per Diode)(T_{CASE} = 25°C unless otherwise stated

Parameter		Test Conditions		Min.	Typ.	Max.	Unit
V_F	Forward Voltage	I_F = 8A	T_J = 150°C			0.8	V
		I_F = 16A	T_J = 25°C			1.0	
I_R	Reverse Current	$V_R = V_{RRM}$	T_J = 150°C			30	mA
		$V_R = V_{RRM}$	T_J = 25°C			500	µA
C_d	Junction Capacitance	V_R = 5 V	f = 1 MHz		500		pF

Pulse test tp=300µs δ≤2%

Parameter	.		Unit
$R_{TH(j-a)}$	Maximum Thermal Resistance Junction To Case	both diodes 1.4 per diode 2.3	°C/W
$R_{TH(j-c)}$	Maximum Thermal Resistance Junction To Case	1.3	°C/W